

### **isc Silicon NPN Power Transistor**

## 2SC3685

### DESCRIPTION

- High Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 800V(Min)
- High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

• Designed for ultrahigh-definition color display horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)							
SYMBOL	PARAMETER VALUE		UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	1500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V				
V <sub>EBO</sub>	Emitter-Base voltage	6	V				
lc	Collector Current-Continuous	6	А				
I <sub>CM</sub>	Collector Current-Peak	16	А				
Pc	Collector Power Dissipation @ Tc=25℃	125	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C				

#### 2 PIN 1. BASE 2.COLLECTOR 3. BMITTER TO-3PN package 1 2 3 C E Θ н G D - - R mm DIM MIN MAX А 20.10 19.60 В 15.50 15 С 4.70 4.90 D 0.90 1.10 Ε 1.90 2.10 F 3.40 3.60G 2.90 3.20 Н 3.20 3.40 J 0.595 0.605 Κ 20.00 20.70 1.90 2.20 Ν 10.89 10. 4.90 Q 5.10 R 3.35 3 45 1.995 S 2,100 5.90 U 10 Y 9.90

### isc website: www.iscsemi.com 1



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### ELECTRICAL CHARACTERISTICS

#### $T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	800			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	8			

#### Switching Times

t <sub>stg</sub>	Storage Time			3.0	μ <b>S</b>
tr	Fall Time	− I <sub>C</sub> = 4A, I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A		0.2	μs

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